

# 5A HIGH VOLTAGE SCHOTTKY BARRIER RECTIFIER POWERMITE® 3

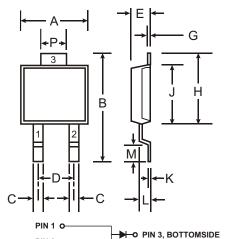
NOT RECOMMENDED FOR NEW DESIGNS USE PDS5100

# Features USE PI

- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Reverse Breakdown Voltage
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

#### **Mechanical Data**

- Case: POWERMITE®3
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: See DiagramMarking: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



PIN 2 O HEAT SINK

Note: Pins 1 & 2 must be electrically connected at the printed circuit board.

POWERMITE®3				
Dim	Min	Max		
Α	4.03	4.09		
В	6.40 6.61			
С	.864	.914		
D	1.83 NOM			
E	1.10	1.14		
G	.173	.203		
Н	5.01	5.17		
J	4.37	4.43		
K	.173	.203		
L	.71	.77		
М	.36	.46		
Р	1.73	1.83		
All Dimensions in mm				

### Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

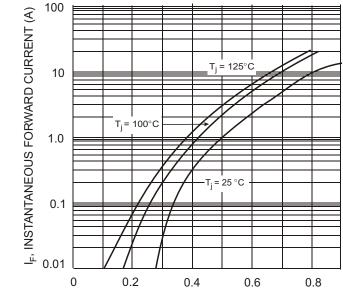
Characteristic	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	V	
RMS Reverse Voltage	V <sub>R(RMS)</sub>	70	V	
Average Rectified Output Current (See also figure 5)	Io	5	Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave Superimposed on Rated Load @ $T_C = 80^{\circ}C$	I <sub>FSM</sub>	100	А	
Typical Thermal Resistance Junction to Case	R <sub>0</sub> JC	1.2	°C/W	
Typical Thermal Resistance Junction to Soldering Point	R <sub>0</sub> JS	2.7	°C/W	
Operating Temperature Range	Tj	-65 to +125	°C	
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C	

#### **Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

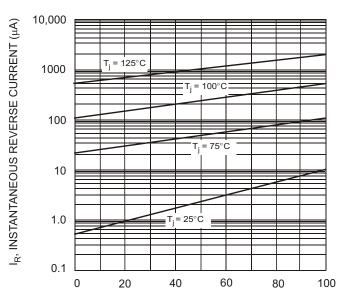
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 1)	V <sub>(BR)R</sub>	100	_	_	V	$I_R = 0.2mA$
Forward Voltage	V <sub>F</sub>		0.75 0.58 0.84 0.67	0.81 0.64 0.90 0.73	V	$\begin{array}{l} I_F = 5A,  T_j =  25^{\circ}C \\ I_F = 5A,  T_j =  125^{\circ}C \\ I_F = 10A,  T_j =  25^{\circ}C \\ I_F = 10A,  T_j =  125^{\circ}C \end{array}$
Peak Reverse Current (Note 1)	I <sub>R</sub>		0.015 2	0.2 100	mA	$T_j = 25^{\circ}C, V_R = 100V$ $T_j = 125^{\circ}C, V_R = 100V$

Notes: 1. Short duration test pulse used to minimize self-heating effect.





V<sub>F</sub>, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 1 Typical Forward Characteristics



V<sub>R</sub>, INSTANTANEOUS REVERSE VOLTAGE (V) Fig. 2 Typical Reverse Characteristics

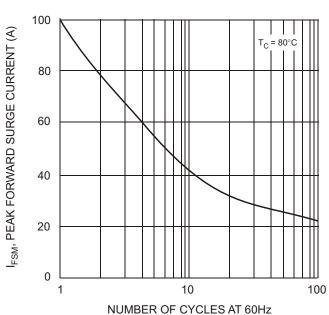


Fig. 3 Max Non-Repetitive Peak Forward Surge Current

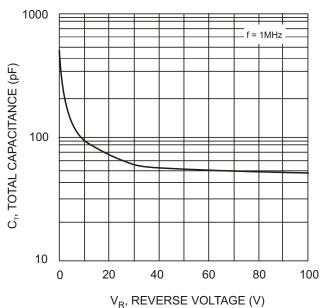
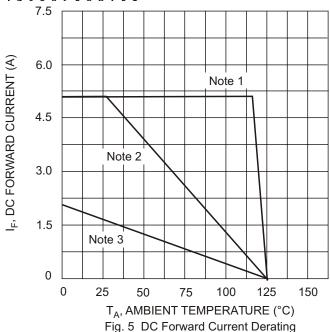
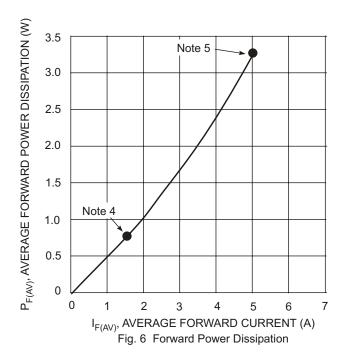


Fig. 4 Typical Capacitance vs.
Reverse Voltage

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Notes:

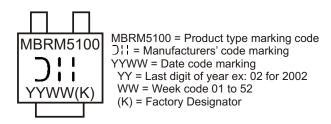
- 1.  $T_A = T_{SOLDERING\ POINT},\ R_{\theta JS} = 2.7^{\circ} C/W,\ R_{\theta SA} = 0^{\circ} C/W.$
- 2. Device mounted on GETEK substrate, 2"x2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0".  $R_{\theta,JA}$  in range of 20-40°C/W.
- Device mounted on FR-4 substrate, 2"x2", 2 oz. copper, single-sided, pad layout as per Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. R<sub>θJA</sub> in range of 100-140°C/W.
- 4. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 3.
- 5. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 2.

#### **Ordering Information** (Note 6)

Device	Packaging	Shipping
MBRM5100-13	POWERMITE®3	5000/Tape & Reel

Notes: 6. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



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POWERMITE is a registered trademark of Microsemi Corporation.